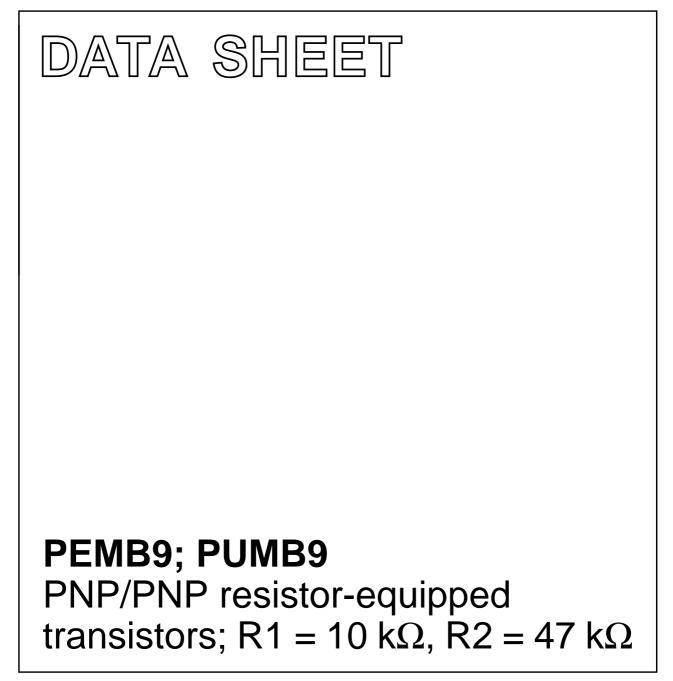
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2003 Feb 03 2003 Oct 03



## PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

### PEMB9; PUMB9

#### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### **APPLICATIONS**

- Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

#### DESCRIPTION

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PACKAGE			NPN/PNP	NPN/NPN	
ITPE NUMBER	PHILIPS	EIAJ		COMPLEMENT	COMPLEMENT	
PEMB9	SOT666	_	Z6	PEMD9	PEMH9	
PUMB9	SOT363	SC-88	B*9	PUMD9	PUMH9	

#### Note

1. \* = p: Made in Hong Kong.

\* = t: Made in Malaysia.

\* = W: Made in China.

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
ITPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION		
PEMB9	6 5 4	1	emitter TR1		
PUMB9		2	base TR1		
	R1 R2	3	collector TR2		
		4	emitter TR2		
		5	base TR2		
		6	collector TR1		
	1 2 3 Top view MAM477				

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-	-50	V
I <sub>O</sub>	output current (DC)	_	-100	mA
TR1	PNP	_	-	_
TR2	PNP	_	_	_
R1	bias resistor	10	_	kΩ
R2	bias resistor	47	-	kΩ

#### Product specification

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

## PEMB9; PUMB9

#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE			
	NAME	DESCRIPTION	VERSION		
PEMB9	<ul> <li>plastic surface mounted package; 6 leads</li> <li>SO</li> </ul>		SOT666		
PUMB9	<ul> <li>plastic surface mounted package; 6 leads</li> <li>SOT363</li> </ul>		SOT363		

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT
Per transis	stor				-
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-10	V
VI	input voltage positive negative			+6 -40	V V
I <sub>O</sub>	output current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device	)				•
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	-	300	mW
	SOT666	notes 1 and 2	-	300	mW

#### Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

## PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

## PEMB9; PUMB9

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or	•		
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

#### Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

#### CHARACTERISTICS

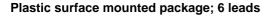
 $T_{amb}$  = 25 °C unless otherwise specified.

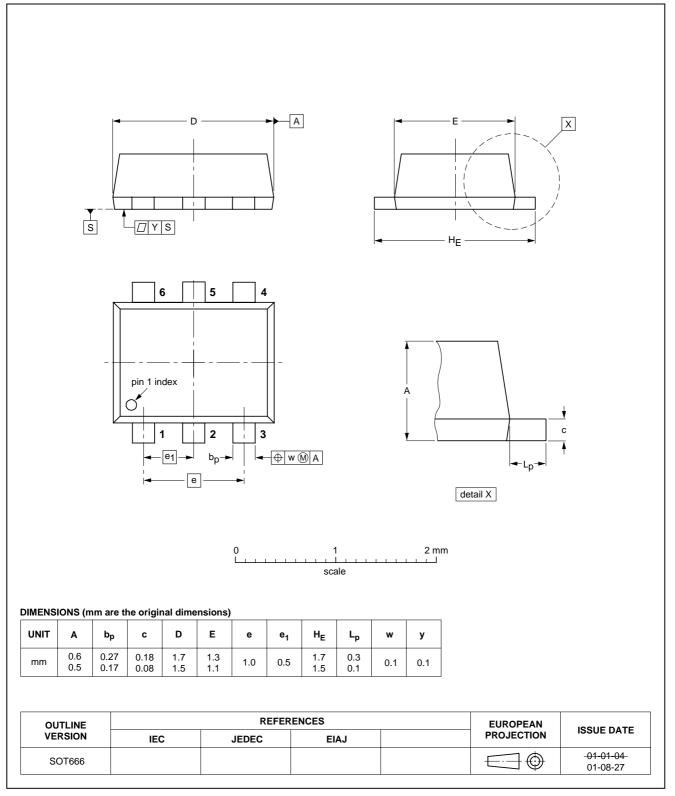
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{\text{E}} = 0$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0$	-	-	-1	μA
		$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 V; I_{C} = 0$	-	-	-150	μA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -5 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	saturation voltage	$I_{\rm C} = -5 \text{ mA}; I_{\rm B} = -0.25 \text{ mA}$	-	-	-100	mV
V <sub>i(off)</sub>	input-off voltage	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -100 \mu\text{A}$	-	-0.7	-0.5	V
V <sub>i(on)</sub>	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_C = -1 \text{ mA}$	-1.4	-0.8	-	V
R1	input resistor		7	10	13	kΩ
R2 R1	resistor ratio		3.7	4.7	5.7	
C <sub>c</sub>	collector capacitance	$I_{E} = i_{e} = 0; V_{CB} = -10 \text{ V};$ f = 1 MHz	-	-	3	pF

PEMB9; PUMB9

## PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

#### PACKAGE OUTLINES





SOT666

## PNP/PNP resistor-equipped transistors; $R1 = 10 \text{ k}\Omega$ , $R2 = 47 \text{ k}\Omega$

## PEMB9; PUMB9

#### SOT363 Х В А □ у Η<sub>E</sub> = v M A 5 Q pin 1 index A<sub>1</sub> 3 1 2 t С 1 • 🕂 w 🕅 B e<sub>1</sub> bp' Lp е detail X 0 1 2 mm scale DIMENSIONS (mm are the original dimensions) A1 UNIT D Е Q Α bp с е e<sub>1</sub> ${}^{\rm H}{\rm E}$ Lp v w у max 0.30 2.2 1.8 1.35 1.15 0.25 0.45 0.25 2.2 2.0 1.1 0.1 1.3 0.65 0.2 0.2 0.1 mm 0.8 0.20 0.10 0.15 0.15 REFERENCES OUTLINE VERSION EUROPEAN **ISSUE DATE** PROJECTION IEC JEDEC EIAJ $\square \bigcirc$ SOT363 SC-88 97-02-28

#### Plastic surface mounted package; 6 leads

## PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

### PEMB9; PUMB9

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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